SONY

CXA3541N

2-channel Read/Write Amplifier for GMR-Ind Head Hard Disk Drive

Description

The CXA3541N is a read/write amplifier for GMR-Ind (Giant Magneto Resistive-Inductive) heads used in hard disk drives, and is capable of supporting up to two channels.

Features

- +5V and –3V power supply
- Current bias voltage sense type
- Low power 180mW at read
- Differential read amplifier gain; ×100/135 (R_{MR} = 50Ω)
- Input noise of 0.77nV/$\sqrt{Hz}$ (typ.), R_{MR} = 50Ω, I_B = 5.9mA
- Recovery time write to read; 300ns (typ.)
- Write data is triggered by differential P-ECL signal
- Servo bank write
- Write unsafe detection circuit
- Serial port
  - Head selection
  - MR bias
  - Write current

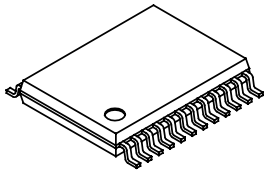
Applications

Hard disk drives with GMR-Ind heads

Structure

Bipolar silicon monolithic IC

24 pin SSOP (Plastic)



Absolute Maximum Ratings (Ta = 25°C)

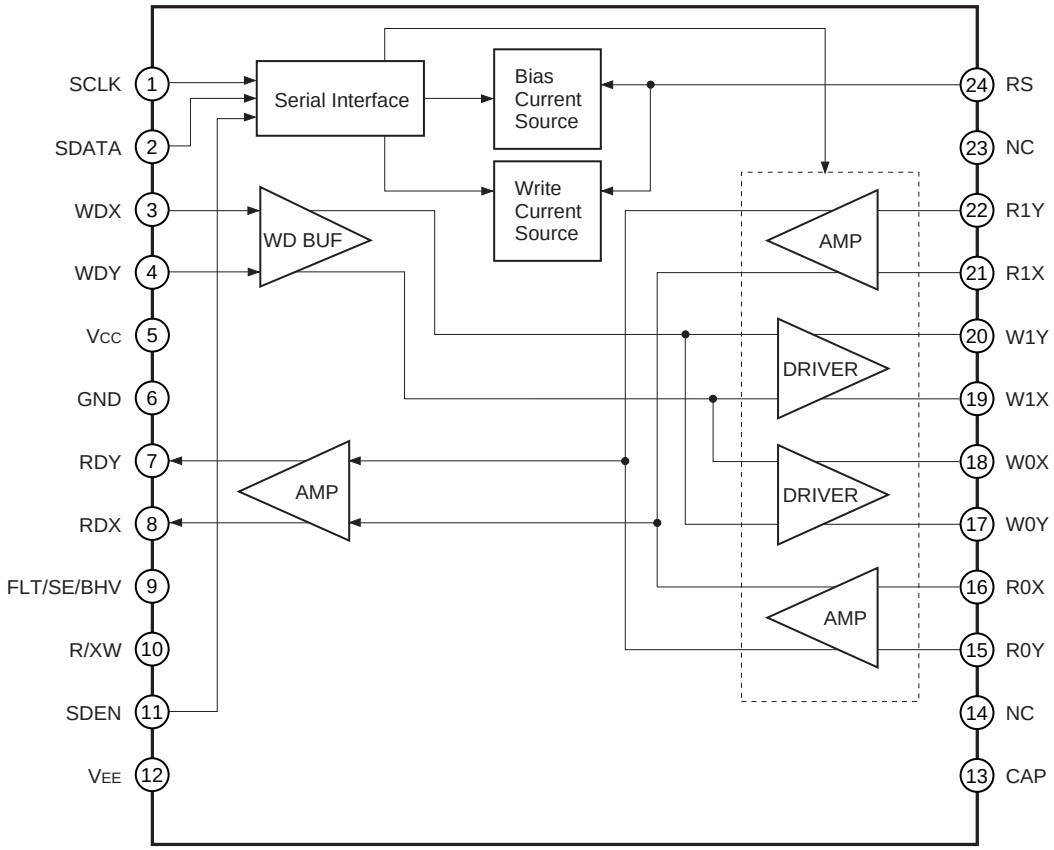
• Supply voltage	V_{CC}	–0.3 to +5.8	V
• Supply voltage	V_{EE}	–3.7 to +0.3	V
• Digital input voltage	Vdi	–0.3 to V_{CC} + 0.3	V
• Operating temperature	Topr	0 to +70	℃
• Storage temperature	Tstg	–55 to +150	℃
• Allowable power dissipation	P_D	800 (on board)	mW

Operating Conditions

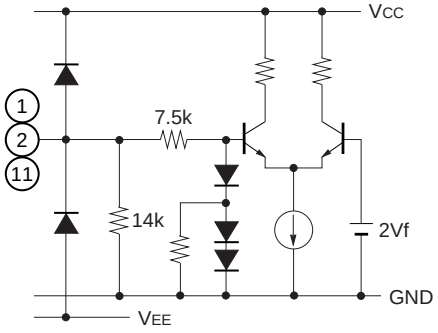
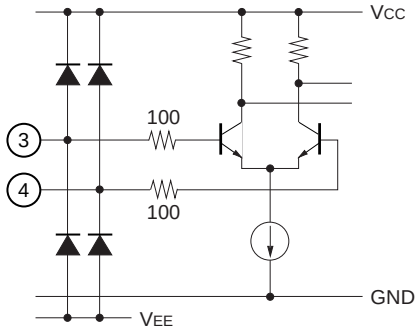
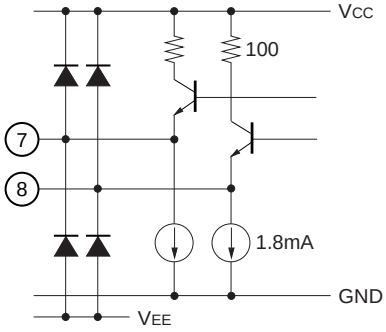
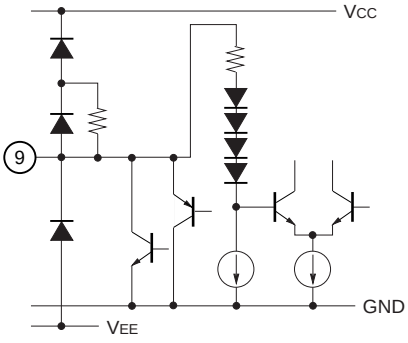
• Supply voltage	V_{CC}	4.4 to 5.5	V
	V_{EE}	–3.5 to –2.6	V
• MR bias voltage	V_{MR}	–300 to +300	mV
• Bias current	I_B	3 to 8	mA
• Write current	I_W	19.5 to 49.5	mA

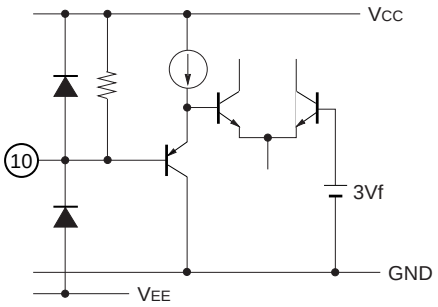
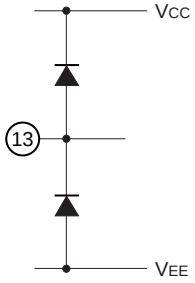
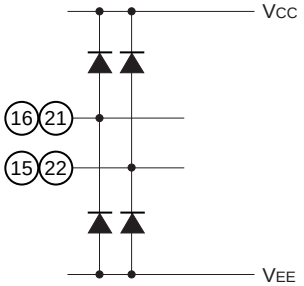
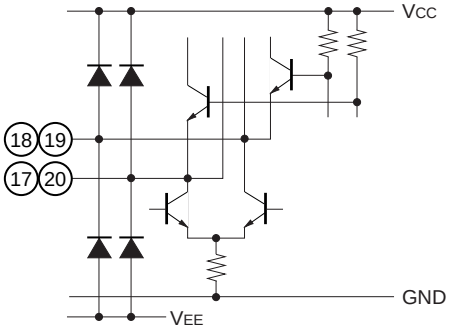
E00205-PS

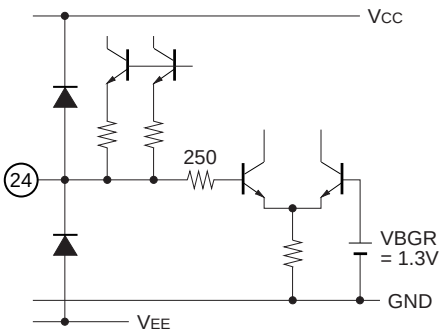
Block Diagram and Pin Configuration



Pin Description

Pin No.	Symbol	Equivalent circuit	Description
1 2 11	SCLK SDATA SDEN		Serial control signal input.
3 4	WDX WDY		Differential P-ECL write data input.
5	Vcc		5V power supply.
6	GND		Ground.
7 8	RDY RDX		Read amplifier output with coupling capacitors. High impedance in the write mode.
9	FLT/SE/BHV		Head unsafe detection output. Servo bank write enable input. Buffered head voltage output.

Pin No.	Symbol	Equivalent circuit	Description
10	R/XW		Read/write control signal input. Read when high, write when low.
12	VEE		–3V power supply.
13	CAP		Connect an external capacitor of read amplifier between this pin and VEE.
14 23	NC		Non connection.
16 15 21 22	R0X R0Y R1X R1Y		MR heads for read. Two channels are provided.
18 17 19 20	W0X W0Y W1X W1Y		Inductive heads for write. Two channels are provided.

Pin No.	Symbol	Equivalent circuit	Description
24	RS		Bias current setting register is connected between this pin and GND.

Electrical Characteristics

(Unless otherwise specified; V_{CC} = 5V, V_{EE} = –3V, Ta = 25°C, CAP = 0.1µF, RS = 7.5kΩ)

No.	Item	Symbol	Measurement conditions	Min.	Typ.	Max.	Unit
Power Dissipation I_W = 29.5mA, I_B = 5.9mA							
1-1	V_{CC} power supply current	I_{SP1}	Sleep mode		2.15	2.85	mA
1-2		I_{ID1}	Idle mode		22	29	mA
1-3		I_{RE1}	Read mode		37	48	mA
1-4		I_{WR1}	Write mode		98	130	mA
1-5	V_{EE} power supply current	I_{ID2}	Idle mode		10	13	mA
1-7		I_{RE2}	Read mode		10	13	mA
1-8		I_{WR2}	Write mode		10	13	mA
1-9	Bank write mode	I_{CCBW}	$I_{CCBW} = 17 + 17 \times N + I_W \times N$ I_W = 29.5mA	—	111	—	mA
Digital Inputs							
2-1	TTL input low input voltage	V_{IL}	TTL input; R/XW Internal pull-up resistor	0		0.8	V
2-2	TTL input high input voltage	V_{IH}		2.0		V_{CC} + 0.3	V
2-3	TTL input input current	I_{TTL}	High voltage: 5V Low voltage: 0V	–200		200	µA
2-4	Serial interface input low input voltage	V_{SIL}	Serial input; SDATA, SCLK, SDEN			0.8	V
2-5	Serial interface input high input voltage	V_{SIH}		2.35			V
2-6	Serial interface input input current	V_{ST}	High voltage: 3.3V Low voltage: 0V Pull-down resistor: 14kΩ	–500		500	µA
3-1	P-ECL common voltage	V_{PC}	$(V_H + V_L)/2$	1.55		V_{CC}	V
3-2	P-ECL differential voltage	V_{PD}	$(V_H – V_L)$	0.2		1.5	V
3-3	P-ECL high voltage	V_{PH}				V_{CC}	V
3-4	P-ECL input current	I_{WD}	Input voltage: 4V	–20		20	µA
Power Dissipation I_W = 29.5mA, I_B = 5.9mA							
4-1	Bank write enable voltage	V_{SEH}		V_{CC} + 1.2		V_{CC} + 1.4	V
4-2	Bank write enable current	I_{SEH}		6		14	mA
5-1	FLT output low voltage	V_{FLTL}	Open collector output External resistance = 2.4kΩ			0.8	V
5-2	FLT output high voltage	V_{FLTH}	Open collector output External resistance = 2.4kΩ	4.5			V
6	BHV gain accuracy	E_{BHV}	$V_{BHV} = V_{CC} – 4 \times I_B \times (R_{MR} + 5.5Ω)$ I_B = "111", R_{MR} = 50Ω	–8		8	%

No.	Item	Symbol	Measurement conditions	Min.	Typ.	Max.	Unit
Read Characteristics R_{MR} = 50Ω, I_B = 5.9mA							
R1	Low gain	A_{VL}	Gain = 0 R_{MR} = 50Ω, I_B = 5.9mA	82	100	118	V/V
R2	High gain	A_{VH}	Gain = 1 R_{MR} = 50Ω, I_B = 5.9mA	110	135	160	V/V
R3	Low frequency cut-off (–3dB)	F_{CL}			350	550	kHz
R4	High frequency cut-off (–3dB)	F_{CH}		140	200		MHz
R5	Input reflected noise	E_{Ni}	Exclusive of head noise R_{MR} = 50Ω, I_B = 5.9mA		0.77	0.95	$\frac{nV}{\sqrt{Hz}}$
R6	MR bias current range 1	I_{BR1}		3		8	mA
R7	MR bias accuracy	E_{IB}		–7		+7	%
R8	MR bias resolution	R_{IB}	3-bit DAC	—	0.714	—	mA
R9-1	V_{CC} power supply rejection ratio	PSRR1	Ripple voltage: 100mVp-p 100kHz to 50MHz	38			dB
R9-2	V_{EE} power supply rejection ratio	PSRR2	Ripple voltage: 100mVp-p 100kHz to 10MHz	45			dB
R10-1	Common mode rejection ratio 1	CMRR1	Ripple voltage: 100mVp-p 100kHz to 50MHz	37			dB
R10-2	Common mode rejection ratio 2	CMRR2	Ripple voltage: 100mVp-p 51MHz to 80MHz	27			dB
R11	Control line input noise rejection	CLRR	Ripple voltage: 100mVp-p 4MHz to 80MHz	40			dB
R12	RDX/RDY offset difference magnitude	V_{OFF1}	Write to read			50	mV
R13	RDX/RDY output impedance	RDro	Differential, read mode	30		100	Ω
Read Safety Characteristics							
P1	MR head open threshold	MRop	Head X – Head Y	600	750	900	mV
P2	MR head short threshold	MRsh	Head X – Head Y I_B = "000" to "011"	15	50	90	mV
Write Characteristics							
W1	Write current range	I_{WR}	DAC code = x "0000" to x "1111"	19.5		49.5	mA
W2	Write current accuracy	E_{IW}	R_H = 0Ω	–7		+7	%
W3	Write current resolution	R_{IW}	4-bit DAC	—	2	—	mA
W4	Leakage current	I_{LEAK}	Unselected head			200	µA
W6	Damping resistor	R_D		800	1000	1200	Ω
W7	Write current propagation delay time	Tpd	L_H = 0, R_H = 0 Write data to 50% of write current			10	ns
W8	Write current rise/fall time	T_R/T_F	R_H = 15Ω, L_H = 150nH, I_W = 25mA	—	1.9	—	ns
W9	Erase current accuracy	E_{IE}	V_{CC} = 3.5V DAC code = x "0101"	–18	–9	0	%
W10	Bank write current accuracy		Refer to Fig.				

No.	Item	Symbol	Measurement conditions	Min.	Typ.	Max.	Unit
Write Safety Characteristics							
U1	Write head open threshold	Rop	Detect open head		1.2	1.4	V
U2	Head voltage when short to GND	V_G	Detect short to GND			0.1	V
U3	WD frequency too low	f_{WDL}		0.5		1.8	MHz
U4	Write safety detect time	Tws	T1: 2 transitions on WDX/WDY			300 + T1	ns
U5	Low V_{CC} threshold	V_{WthL}	Fault detected	3.7	3.9	4.1	V
U6	Low V_{CC} threshold	V_{WthH}	Fault removed	3.9	4.1	4.3	V
U7	Low V_{CC} threshold hysteresis	Vhys		—	200	—	mV
Switching Characteristics		Iw = 29.5mA, I_B = 5.9mA					
S1	Write to Read	T_{WR}	Signal on WDX/WDY 90% RD signal or 10% Iw		300	500	ns
S2	Read to Write	T_{RW}	90% Iw		50	70	ns
S3	Idle to Read	T_{IR}	90% RD signal			1.0	µs
S4	Sleep to Read	T_{SR1}	90% RD signal, 90% I_B*1 I_B = "011"		600	2000	µs
Bank Write Characteristics		Iw = 29.5mA, I_B = 5.9mA					
S5	Read to Bank write	T_{RB}	90% Iw			100	ns
S6	Bank write to Read	T_{BR}	10% Iw			100	ns
S7	Idle to Bank write Idle to Write	T_{IW}	90% Iw			300	µs
Serial Port Timing							
B1	Setup time	T_{SU} (sden)	SDEN to first SCLK	30			ns
B2	Hold time	Th (sden)	Last SCLK to deassert SDEN	15			ns
B4	SCLK frequency	f (sclk)				30	MHz
B5	SCLK pulse width	Tw (sclk)		10			ns
B6	SCLK – SDATA setup time	T_{SU} (d)		10			ns
B7	SCLK – SDATA hold time	Th (d)		10			ns
B8	SDEN low time	T_{SL}		100			ns

*1 T_{SR} is proportional to I_B and external CAP value.

Serial Port Characteristics

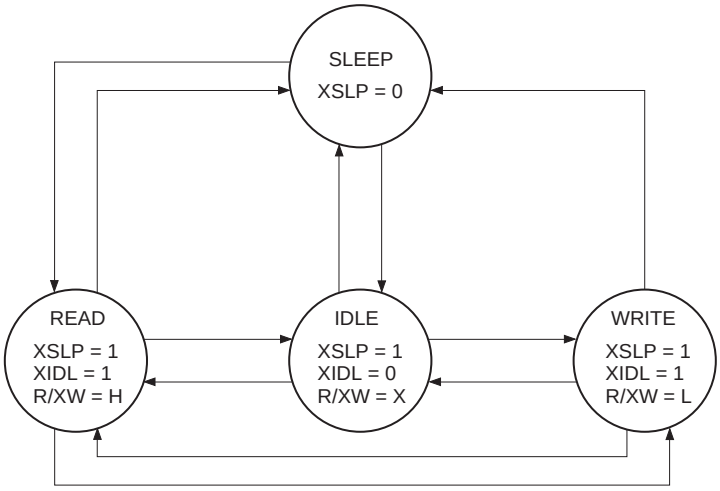
ADR1	ADR0	DATA5	DATA4	DATA3	DATA2	DATA1	DATA0
0	0	XSLP	XIDL	N/A	N/A	N/A	HS
0	1	GAIN	BHV	N/A	IB2	IB1	IB0
1	0	MROPN	MRSHT	IW3	IW2	IW1	IW0

* IB[2:0] bits are initialized by "0" at power on.

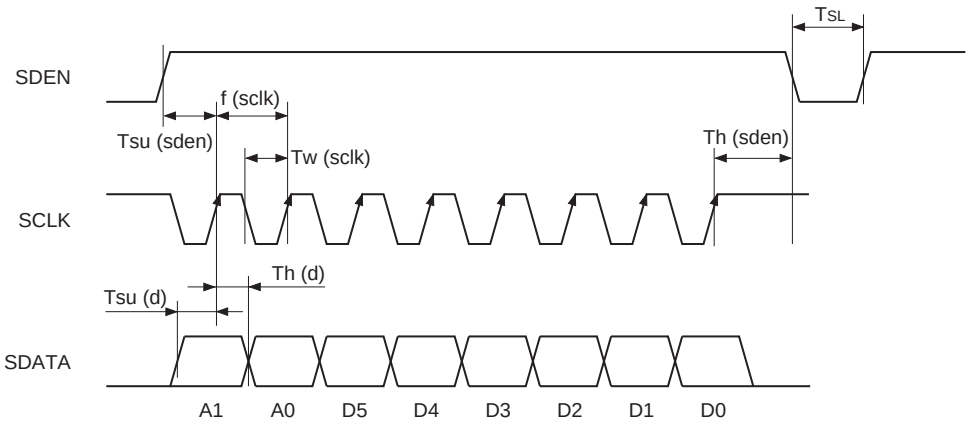
Code Description

Bit	Function
XSLP	0 = Set the pre-amplifier into low power "sleep" mode.
XIDL	0 = Set pre-amplifier to idle mode.
HS	Head select bit.
GAIN	Set the pre-amplifier to high or low gain mode. 1 = Set pre-amplifier to high gain mode.
BHV	Active the BHV test point pin. "1" active.
IB[2:0]	MR bias current set.
MROPN	1 = Set MR head open detector active.
MRSHT	1 = Set MR head short detector active.
IW[3:0]	Set write current.

Mode Control



Serial Port Timing Detail



Serial Port Timing

After the SDEN goes high, the last eight bits are transferred into the register. The SCLK will shift the data presented at SDATA into an internal shift register on the rising edge of each clock.
As SCLK initial condition, both of low and high signal is acceptable.

Unsafe Condition

1. Write fault condition
   FLT is a high level in write fault condition.
   • Open write head leads. f_{WD} < 15MHz
   • Write head leads shorted to ground.
   • WD frequency is too low.
   • Power supply is out of tolerance.
2. Read fault condition
   FLT is a low level in read fault condition.
   • Open short MR head. (This function is set by serial resister.)

Bank Write Control (Refer to Bank "Write current vs. Current accuracy" characteristic curve)

1. Set the read mode.
2. Force a certain voltage (min. V_{CC} + 1.2V) to FLT/SE pin by using the pull-up register. (R_{SE} = 820Ω)
   #This operation disables all fault detection.
3. Set V_{CC} at 3.5V (in case of the erase mode only)
4. Start the write operation by setting R/XW = L.
5. Terminate the write operation by setting R/XW = H.
   i) Allow 50% write duty or less.
   ii) Low voltage detector is disabled in the bank write mode and erase mode.
   iii) Don't change the serial register data bits in following conditions:
      • V_{CC} = 3.5V
      • On entering write data.

BHV (Buffered Head Voltage)

1. Applicable within V_{CC} = 5V ± 5%.
2. Turn BHV on, but turn off MROPN and MRSHT.
3. V_{BHV} is determined by basis of V_{CC}. $V_{BHV} = V_{CC} – (4 \times I_B \times (R_{MR} + 5.5\Omega))$

Head Condition

1. Short X-Y terminal on un-used write head.
2. Recommended X-Y terminal on un-used read head short.

Polarity

1. Read output signal on RDX is negative, when MRX is positive by increasing R_{MR}.
2. Write current flows into X side, when WDX is high and WDY is low.

Head Select Table
(2ch)

HS	Normal operation
0	0
1	1

MR Bias

IB2	IB1	IB0	I_B [mA]
0	0	0	3.0
0	0	1	3.714
0	1	0	4.429
0	1	1	5.143
1	0	0	5.857
1	0	1	6.571
1	1	0	7.286
1	1	1	8.0

Write Current

IW3	IW2	IW1	IW0	Write current [$mA_{0\text{-}P}$]
0	0	0	0	19.5
0	0	0	1	21.5
0	0	1	0	23.5
0	0	1	1	25.5
0	1	0	0	27.5
0	1	0	1	29.5
0	1	1	0	31.5
0	1	1	1	33.5
1	0	0	0	35.5
1	0	0	1	37.5
1	0	1	0	39.5
1	0	1	1	41.5
1	1	0	0	43.5
1	1	0	1	45.5
1	1	1	0	47.5
1	1	1	1	49.5

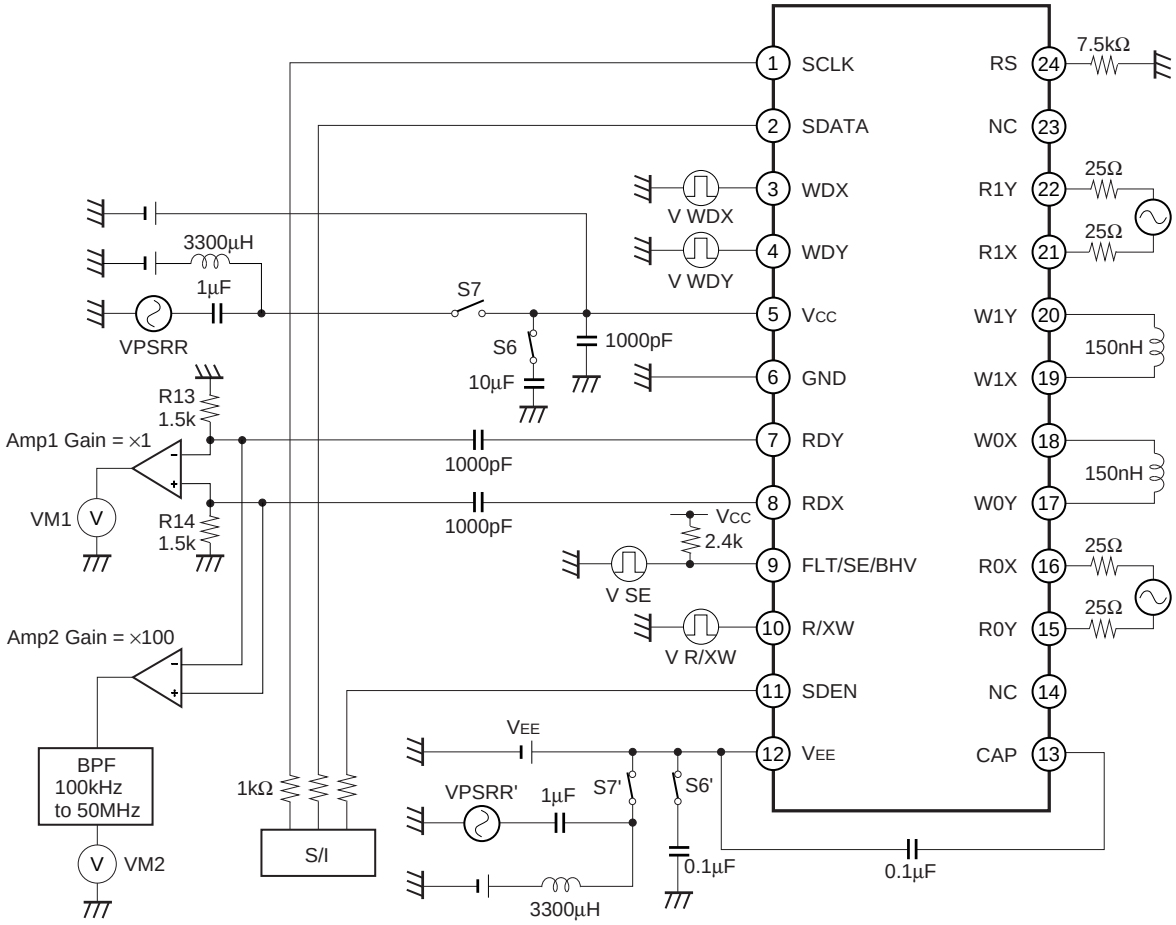
Actual head current is defined by the following equation:

$I_{HEAD} = I_W/(1 + R_H/R_D)$

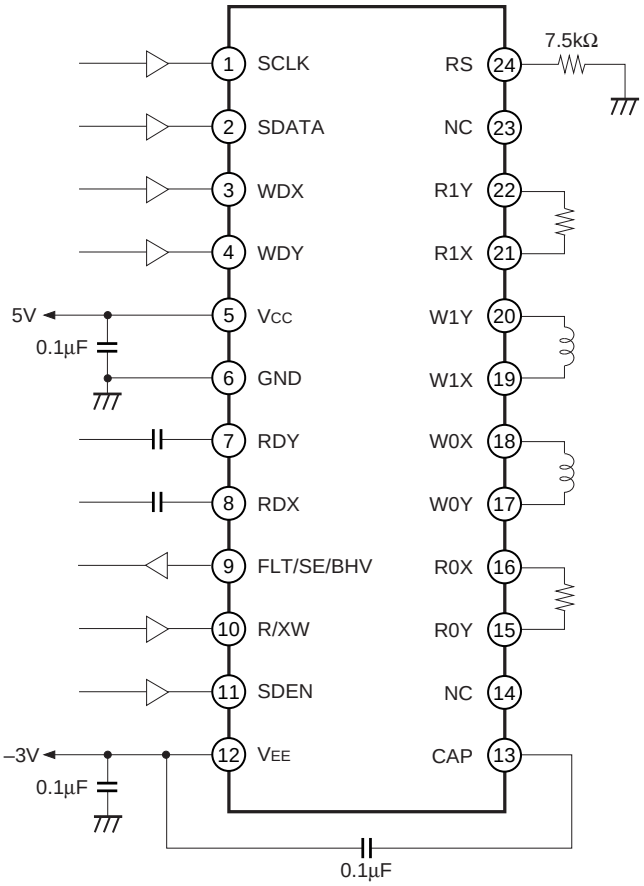
R_H: Head resistance

R_D: Damping resistance

Electrical Characteristics Measurement Circuit

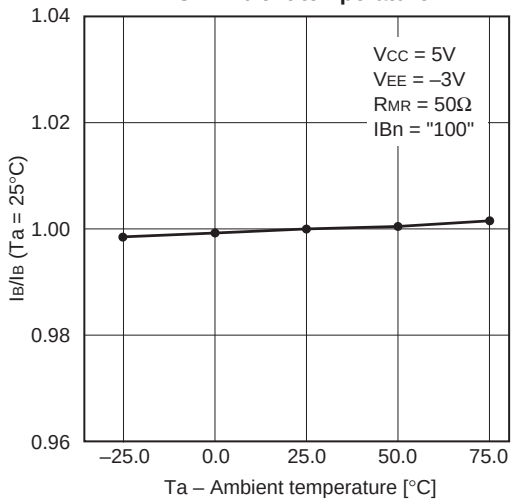


Application Circuit

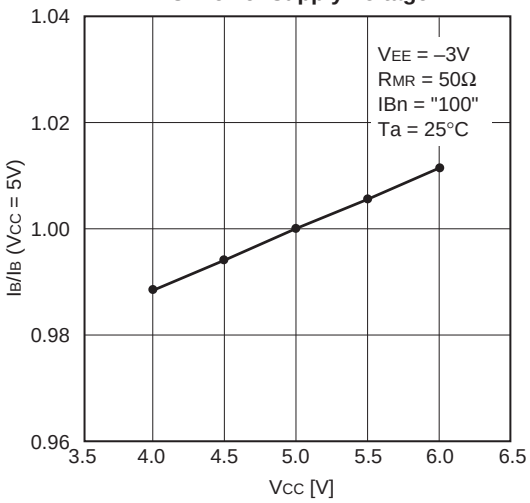


Application circuits shown are typical examples illustrating the operation of the devices. Sony cannot assume responsibility for any problems arising out of the use of these circuits or for any infringement of third party patent and other right due to same.

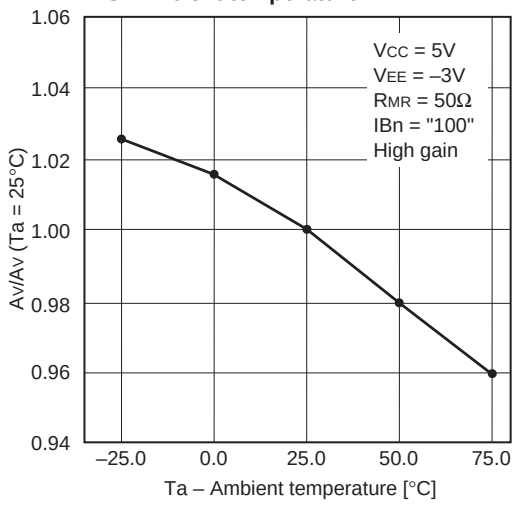
Normalized bias current vs. Ambient temperature



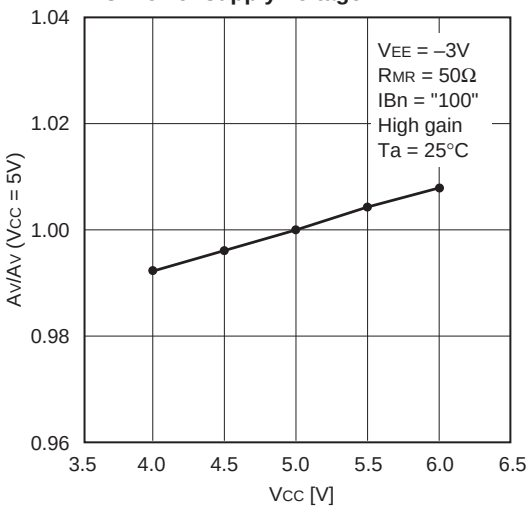
Normalized bias current vs. Power supply voltage



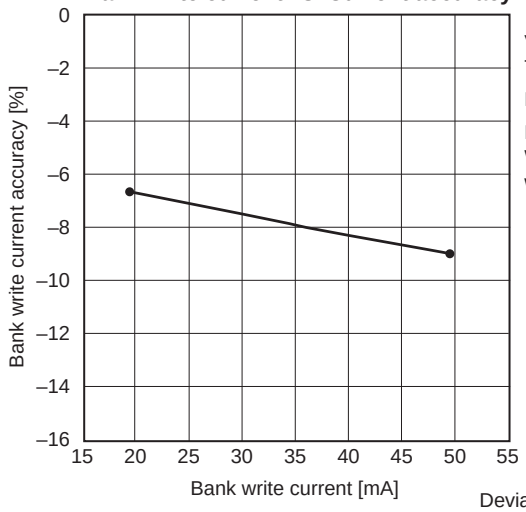
Normalized read amplifier voltage gain vs. Ambient temperature



Normalized read amplifier voltage gain vs. Power supply voltage



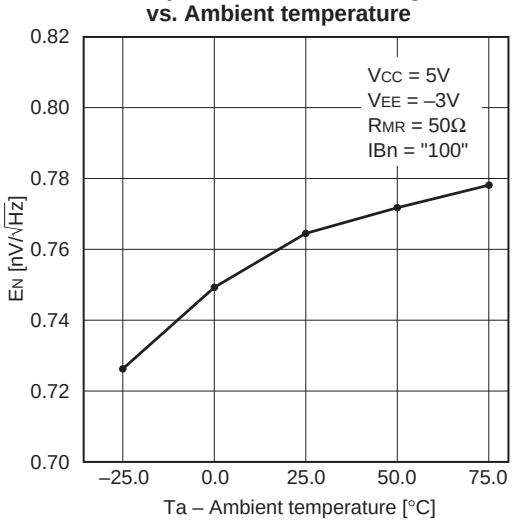
Bank write current vs. Current accuracy



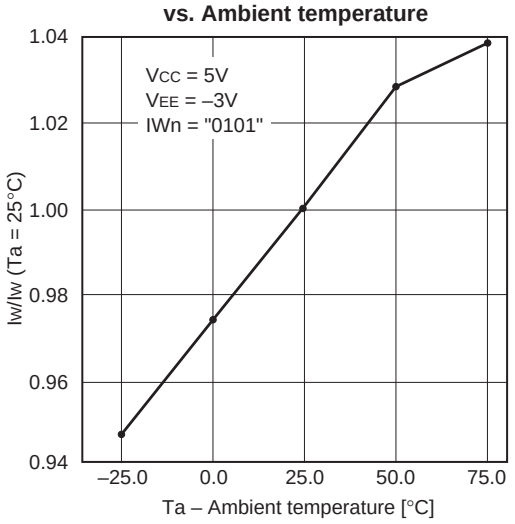
VCC = 5V
Ta = 25°C
RH = 0Ω
Read 170µs
Write 30µs
with Write Data

Deviation of bank write current is within ± 7% at basis of the chart.

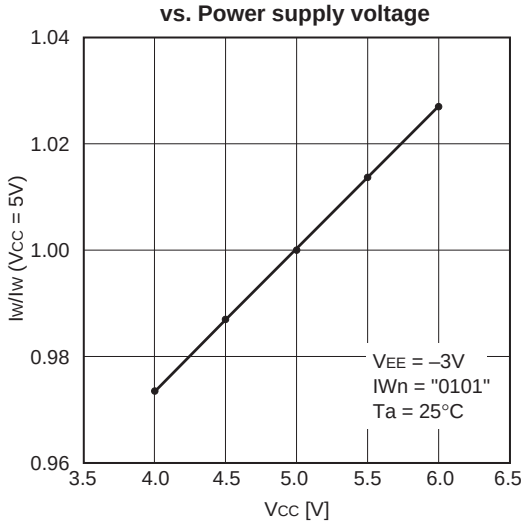
Input refered noise voltage vs. Ambient temperature



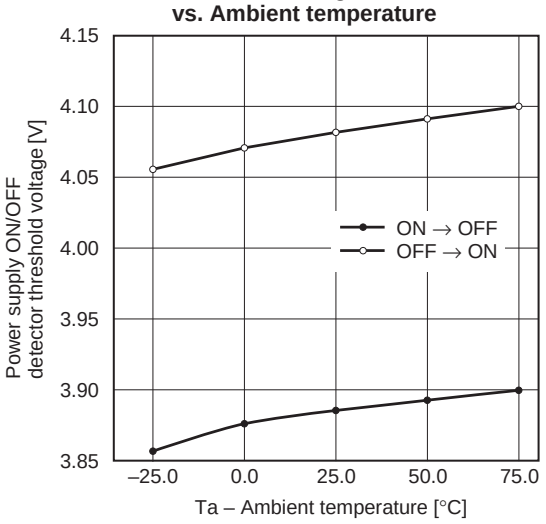
Normalized write current vs. Ambient temperature



Normalized write current vs. Power supply voltage

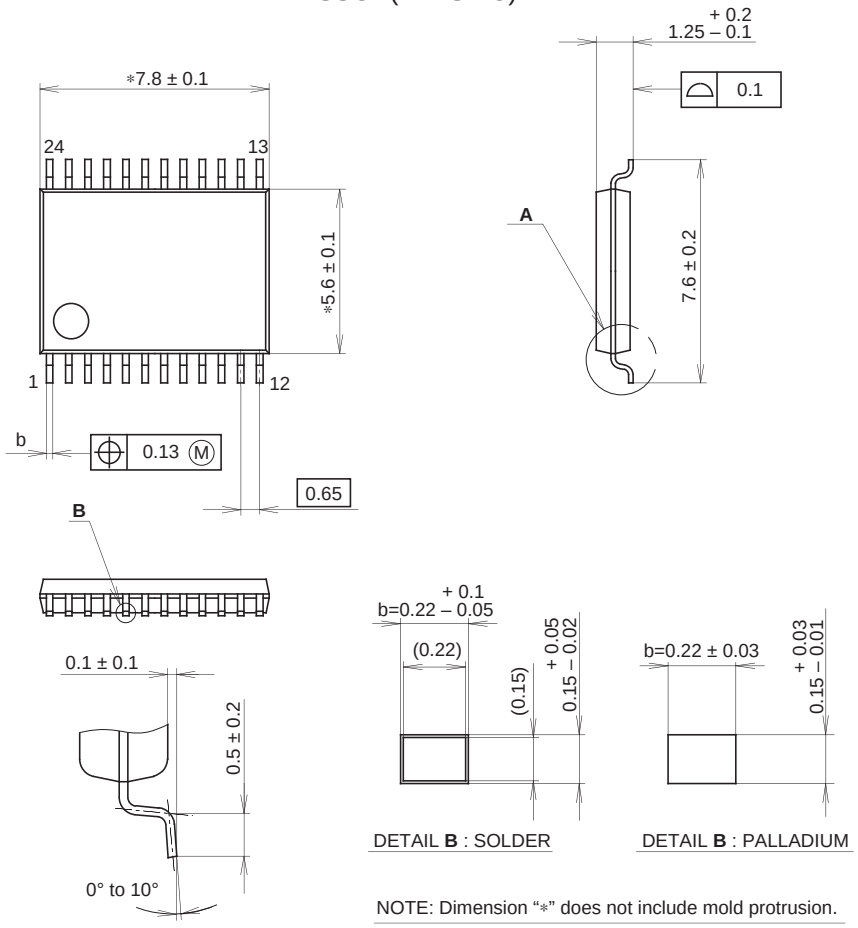


Power supply ON/OFF detector threshold voltage vs. Ambient temperature



Package Outline Unit: mm

24PIN SSOP(PLASTIC)



NOTE: Dimension "∗" does not include mold protrusion.

SONY CODE	SSOP-24P-L01
EIAJ CODE	SSOP024-P-0056
JEDEC CODE	————

PACKAGE STRUCTURE

PACKAGE MATERIAL	EPOXY RESIN
LEAD TREATMENT	SOLDER/PALLADIUM PLATING
LEAD MATERIAL	42/COPPER ALLOY
PACKAGE MASS	0.1g

NOTE : PALLADIUM PLATING
This product uses S-PdPPF (Sony Spec.-Palladium Pre-Plated Lead Frame).